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(74) Agents: KAWAMITAI, Osamu et al.; AOYAMA & PARTNERS, IMP Building, 3-7, Shiromi 1-chome, Chuo-ku, Osaka-shi, Osaka, 5400001 (JP).

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(71) Applicant (for all designated States except US): MATSUSHITA ELECTRIC WORKS, LTD. (JP/JP); 1048, Oaza Kadoma, Kadoma-shi, Osaka, 5718686 (JP).

(72) Inventors: and

(75) Inventors/Applicants (for US only): GOUDA, Kazuo (JP/JP); c/o MATSUSHITA ELECTRIC WORKS, LTD., 1048, Oaza-Kadoma, Kadoma-shi, Osaka, 5718686 (JP). TSUJII, Koji (JP/JP); c/o MATSUSHITA ELECTRIC WORKS, LTD., 1048, Oaza-Kadoma, Kadoma-shi, Osaka, 5718686 (JP). KIRIHARA, Masao (JP/JP); c/o MATSUSHITA ELECTRIC WORKS, LTD., 1048, Oaza-Kadoma, Kadoma-shi, Osaka, 5718686 (JP). NISHIJIMA, Yuuichi (JP/JP); c/o MATSUSHITA ELECTRIC WORKS, LTD., 1048, Oaza-Kadoma, Kadoma-shi, Osaka, 5718686 (JP).

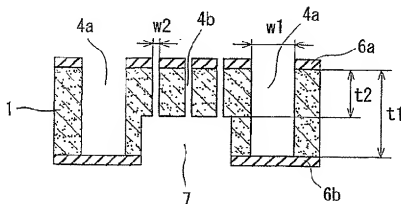
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(54) Title: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE



(57) Abstract: Disclosed is a method of manufacturing a semiconductor device. In this method, a concave portion (7) is formed in one surface in the thickness direction of a primary base plate (1) comprising a semiconductor substrate with a relatively large thickness dimension. Then, through holes (4a, 4b) are formed by a reactive-ion etching process using as a mask an opening (8) formed in an oxide film (6a) provided on the other surface in the thickness direction of the primary base plate (1). The opening (8) has a narrow width in a region

corresponding to the concave portion (7) and a wide width in the remaining region. Thus, respective times necessary for the wide-width through-hole (4a) to penetrate through the primary base plate (1) and necessary for the narrow-width through-hole (4b) to reach a bottom surface of the concave portion (7) can be approximately equalized to complete the common etching process of the wide-width through-hole (4a) and the narrow-width through-hole (4b) approximately simultaneously.